

IGBT module

Engineering Sample SK 25 GD 12T4 ETp

Features

- One screw mounting module
- Solder free mounting with Press-Fit terminals
- Fully compatible with other SEMITOP® Press-Fit types
- Trench4 IGBT technology
- CAL4F technology FWD
- Integrated NTC temperature sensor
- UL recognized, file no. E 63 532

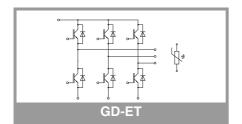
Typical Applications*

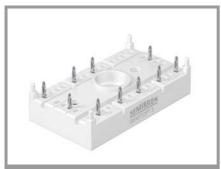
Inverter

Absolute Maximum Ratings						
Symbol	Conditions		Values	Unit		
IGBT 1	•					
V_{CES}	T _j = 25 °C		1200	V		
Ic	T _i = 150 °C	T _s = 25 °C	32	Α		
	1, = 150 0	T _s = 70 °C	25	Α		
Ic	T _j = 175 °C	T _s = 25 °C	35	Α		
		T _s = 70 °C	29	Α		
I _{Cnom}			25	Α		
I _{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		75	Α		
V_{GES}			-20 20	V		
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μs		
Tj			-40 175	°C		

Absolute Maximum Ratings						
Symbol	Conditions		Values	Unit		
Diode 1				'		
V_{RRM}	T _j = 25 °C		1200	V		
l _F	T _i = 150 °C	T _s = 25 °C	25	Α		
	1 - 130 0	T _s = 70 °C	19	Α		
I _F	T 475.00	T _s = 25 °C	28	Α		
	T _j = 175 °C	T _s = 70 °C	22	Α		
I _{Fnom}		<u>, </u>	25	Α		
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		50	Α		
I _{FSM}	10 ms, sin 180°, T _j = 150 °C		100	Α		
Tj			-40 175	°C		

Absolute Maximum Ratings						
Symbol Conditions Values Ur						
Module						
I _{t(RMS)}	T _{terminal} = 100 °C, T _S = 60°C, per pin	40	Α			
T _{stg}		-40 125	°C			
V _{isol}	AC, sinusoidal, t = 1 min	2500	V			





SEMITOP® 3 Press-Fit

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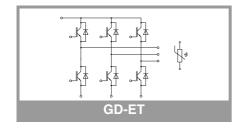
Typical Applications*

• Inverter

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1	IGBT 1					
$V_{\text{CE(sat)}}$	I _C = 25 A	T _j = 25 °C		1.85	2.10	V
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.25	2.45	V
V_{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V
	Chipievei	T _j = 150 °C		0.70	0.80	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		42	48	mΩ
	chiplevel	T _j = 150 °C		62	66	mΩ
$V_{\text{GE(th)}}$	$V_{GE} = V_{CE}, I_{C} = 0.85$	5 mA	5	5.8	6.5	V
I _{CES}	$V_{GE} = 0 V$	T _j = 25 °C			0.67	mA
	V _{CE} = 1200 V			-		mA
C_{ies}	V _{CF} = 25 V	f = 1 MHz		1.43		nF
Coes	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	f = 1 MHz		0.115		nF
C _{res}	I GE - O I	f = 1 MHz		0.085		nF
Q_G	V _{GE} = -7V+15V			142		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		22		ns
t _r	$I_{\rm C} = 25 {\rm A}$	T _j = 150 °C		19.5		ns
E _{on}	$\begin{array}{l} R_{G \text{ on}} = 19 \ \Omega \\ R_{G \text{ off}} = 19 \ \Omega \\ \text{di/dt}_{on} = 2825 \ \text{A/}\mu\text{s} \\ \text{di/dt}_{off} = 2825 \ \text{A/}\mu\text{s} \\ \text{V}_{GE \text{ neg}} = -7 \ \text{V} \\ \text{V}_{GE \text{ pos}} = 15 \ \text{V} \end{array}$	T _j = 150 °C		2.27		mJ
t _{d(off)}		T _j = 150 °C		288		ns
t _f				77.5		ns
E _{off}		T _j = 150 °C		2.7		mJ
R _{th(j-s)}	per IGBT			1.31		K/W

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1						•
V _F	I _F = 25 A	T _j = 25 °C		2.41	2.74	V
	chiplevel	T _j = 150 °C		2.45	2.79	V
V_{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		44	50	mΩ
		T _j = 150 °C		62	68	mΩ
I _{RRM}	I _F = 25 A	T _j = 150 °C		31.5		Α
Q _{rr}	$di/dt_{off} = 2825 \text{ A/}\mu\text{s}$	T _j = 150 °C		1.15		μС
E _{rr}	$V_{GE} = -7 \text{ V}$ $V_{CC} = 600 \text{ V}$	T _j = 150 °C		1.28		mJ
R _{th(j-s)}	per diode			1.91		K/W

Characteristics						
Symbol	Conditions	min.	typ.	max.	Unit	
Module						
Ms	to heatsink	2.25		2.5	Nm	
W	weight		30		g	



Characteristics							
Symbol	ol Conditions min. typ. max.						
Temperatu	ure Sensor						
R ₁₀₀	T _r = 100 °C		493 ± 5%		Ω		
B _{100/125}	$R_{(T)} = R_{100} exp[B_{100/125}(1/T-1/T_{100})]; T[K];$		3550 ±2%		К		

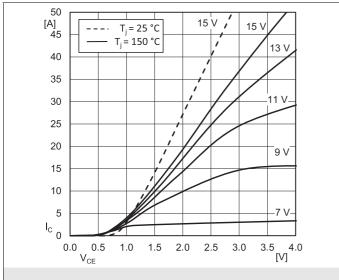


Fig. 1: Typ. IGBT1 output characteristic, incl. R_{CC'+ EE'}

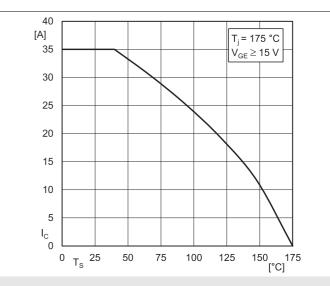


Fig. 2: Typ. rated current vs. temperature $I_C = f(T_S)$

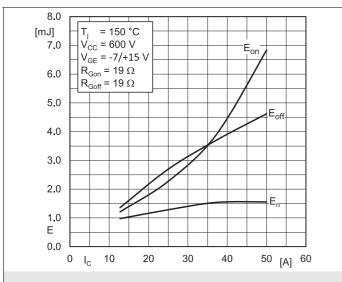


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

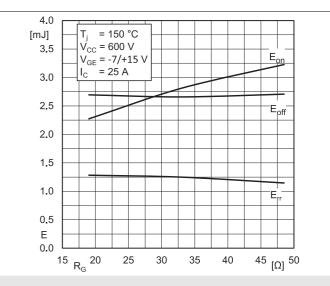


Fig. 4: Typ. turn-on /-off energy = f (R_G)

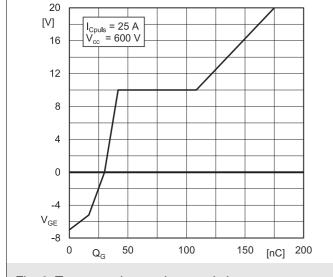


Fig. 6: Typ. gate charge characteristic

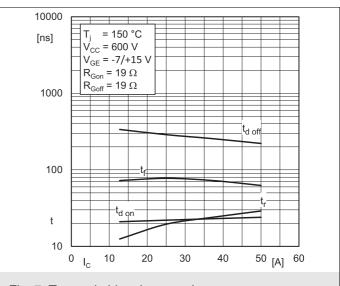
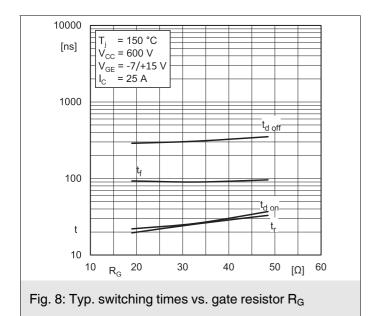


Fig. 7: Typ. switching times vs. I_C



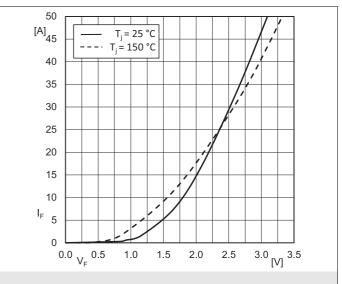
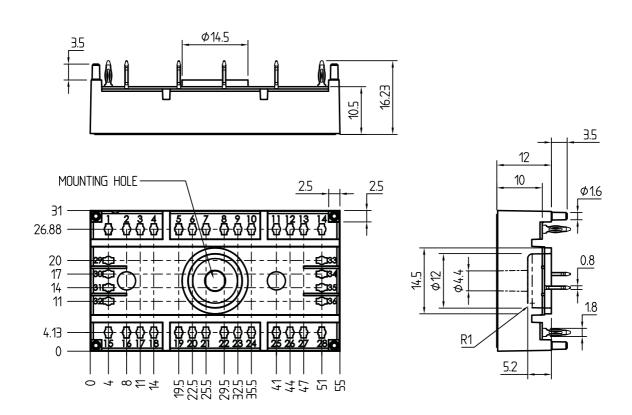


Fig. 10: Typ. CAL diode forward charact., incl. $R_{\text{CC'+}\,\text{EE'}}$

dimensions in mm

tolerance system: ISO 2768-m



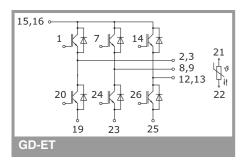
Suggested drilled hole diameter for terminal pins in the circuit board:

minimum: 1.575mmtypical: 1.6mmmaximum: 1.625mm

Suggested hole diameter for the mounting pins in the circuit board: 2mm

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SEMITOP 3 Press-Fit



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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